

page 3 USSN 10/645 292

IN THE CLAIMS

Amend the claims as follows:

1.-22.(canceled)

23.(currently amended) Apparatus for forming a chemical vapor deposition coating gas, comprising means for providing a halide precursor gas, a first source comprising a metal, means for flowing the halide precursor gas in contact with ~~[[a]]~~ the first source ~~comprising a metal to form a first coating gas~~, coating retort means, said first source being disposed outside said coating retort means, and means for flowing the first coating gas into the coating retort means in contact with a source of a reactive element disposed inside the coating retort means to convert a portion of the first coating gas to a halide coating gas of the gettering reactive element that contacts a substrate in the coating retort means with the first coating gas to codeposit the metal and the reactive element on the substrate.

24.(currently amended) The apparatus of Claim 23 including a secondary source of the metal upstream of the reactive element source in the coating retort means for contacting ~~[[the]]~~ an unconverted portion of the first coating gas.

25.(currently amended) The apparatus of Claim 24 including means for introducing another metal halide coating gas into the coating retort means upstream of the ~~gettering reactive~~ element source to codeposit said another metal along with said metal and the reactive element on the substrate.

26.(new) The method of Claim 23 wherein said source of said reactive element comprises particulates comprising at least one of Hf, Zr, Si, and Y.

27.(new) Apparatus for forming a chemical vapor deposition coating gas, comprising means for providing a halide precursor gas, means for flowing the halide precursor gas in contact with a first source comprising a metal to form a first coating gas, coating retort means, means for flowing the first coating gas into the coating retort means in contact with a source of a reactive element disposed inside the coating retort means to convert a portion of the first coating gas to a halide coating gas of the reactive element, and a secondary source of said metal disposed upstream of said source of said reactive element in the coating retort means to contact an unconverted portion of the first coating gas.

28.(new) The method of Claim 27 wherein said source of said reactive element comprises particulates comprising at least one of Hf, Zr, Si, and Y.

29.(new) Apparatus for forming a chemical vapor deposition coating gas, comprising means for providing a halide precursor gas, a first source comprising aluminum, means for flowing the halide precursor gas in contact with the first source to form a first coating gas comprising aluminum halide, a coating retort, said first source being disposed outside said coating retort, and means for flowing the first coating gas into the coating retort in contact with a source of a reactive element disposed inside the coating retort to convert a portion of the first coating gas to a halide coating gas of the reactive element.

30.(new) The apparatus of Claim 29 including a secondary source comprising aluminum inside the coating retort means upstream of the reactive element source for contacting an unconverted portion of the first coating gas.

31.(new) The apparatus of Claim 30 including means for introducing another metal halide coating gas into the coating retort upstream of the reactive element source.

32.(new) The method of claim 30 wherein said source of said reactive element comprises particulates comprising at least one of Hf, Zr, Si, and Y.